MOSFETs Silicon P-Channel MOS (U-MOSVI)

# SSM3J372R

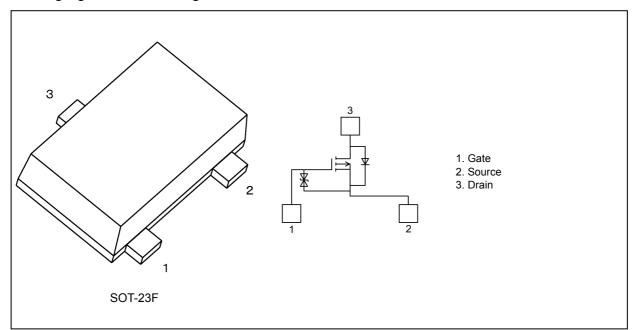
#### 1. Applications

Power Management Switches

#### 2. Features

- (1) AEC-Q101 qualified (Please see the orderable part number list)
- (2) 1.8-V gate drive voltage.
- $\begin{array}{ll} \text{(3)} & \text{Low drain-source on-resistance} \\ & R_{DS(ON)} = 144 \ \text{m}\Omega \ (\text{max}) \ (@V_{GS} = -1.8 \ \text{V}) \\ & R_{DS(ON)} = 72.0 \ \text{m}\Omega \ (\text{max}) \ (@V_{GS} = -2.5 \ \text{V}) \\ & R_{DS(ON)} = 50.0 \ \text{m}\Omega \ (\text{max}) \ (@V_{GS} = -4.5 \ \text{V}) \\ & R_{DS(ON)} = 42.0 \ \text{m}\Omega \ (\text{max}) \ (@V_{GS} = -10 \ \text{V}) \end{array}$

#### 3. Packaging and Pin Configuration



#### 4. Orderable part number

Orderable part number	AEC-Q101		Note	
SSM3J372R,LF	—		General Use	
SSM3J372R,LXGF	YES	(Note 1)	Unintended Use	(Note 1)
SSM3J372R,LXHF	YES		Automotive Use	

Note 1: For more information, please contact our sales or use the inquiry form on our website.

#### 5. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25^{\circ}$ C)

	Characteristics		Symbol	Rating	Unit
Drain-source voltage			V <sub>DSS</sub>	-30	V
Gate-source voltage			V <sub>GSS</sub>	-12/+6	
Drain current (DC)		(Note 1)	Ι <sub>D</sub>	-6.0	A
Drain current (pulsed)		(Note 1,2)	I <sub>DP</sub>	-24.0	
Power dissipation		(Note 3)	PD	1	w
Power dissipation	(t < 10 s)	(Note 3)	PD	2	W
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Pulse width (PW)  $\leq$  1 ms, duty  $\leq$  1%

- Note 3: Device mounted on an FR4 board.(25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm, Cu Pad: 645 mm<sup>2</sup>)
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

#### 6. Thermal Characteristics

Characteristics		Symbol	Max	Unit
Channel-to-ambient thermal resistance	(Note 1)	R <sub>th(ch-a)</sub>	125	°C/W

Note 1: Device mounted on an 25.4 mm × 25.4 mm × 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm<sup>2</sup>)

#### 7. Electrical Characteristics

#### 7.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	V <sub>GS</sub> = -10/+6 V, V <sub>DS</sub> = 0 V	—	_	±1	μA
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V	—		-1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V	-30		_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 8 V	-22	_	_	
Gate threshold voltage	(Note 2)	V <sub>th</sub>	V <sub>DS</sub> = -3 V, I <sub>D</sub> = -1 mA	-0.5	_	-1.2	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	I <sub>D</sub> = -5.0 A, V <sub>GS</sub> = -10 V	_	36.0	42.0	mΩ
			I <sub>D</sub> = -4.0 A, V <sub>GS</sub> = -4.5 V	_	42.5	50.0	
			I <sub>D</sub> = -2.5 A, V <sub>GS</sub> = -2.5 V	_	57.5	72.0	
			I <sub>D</sub> = -0.5 A, V <sub>GS</sub> = -1.8 V	_	76.5	144	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	V <sub>DS</sub> = -3 V, I <sub>D</sub> = -2.5 A	5.7	11.3	_	S

Note 1: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

Note 3: Pulse measurement.

#### 7.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15 V, V <sub>GS</sub> = 0 V,	_	560	—	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	65	_	
Output capacitance	C <sub>oss</sub>			80		
Switching time (turn-on time)	t <sub>on</sub>	V <sub>DD</sub> = -15 V, I <sub>D</sub> = -2.0 A V <sub>GS</sub> = 0 to -4.5 V, R <sub>GS</sub> = 10 Ω		15	_	ns
Switching time (turn-off time)	t <sub>off</sub>	Duty $\leq$ 1%, Input: t <sub>r</sub> , t <sub>f</sub> < 5 ns Common source, See Chapter 7.3		75		

#### 7.3. Switching Time Test Circuit

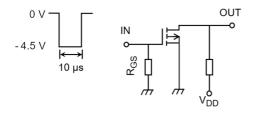
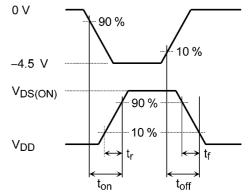


Fig. 7.3.1 Test Circuit of Switching Time	Fig. 7.3.1	Test Circuit of Switching Time
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Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (-1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

#### 7.4. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	3	V <sub>DD</sub> = -15 V, V <sub>GS</sub> = -4.5 V,	_	8.2		nC
Gate-source charge 1	Q <sub>gs1</sub>	I <sub>D</sub> = -6.0 A	_	1.1	_	
Gate-drain charge	Q <sub>gd</sub>		_	2.2	_	

### 7.5. Source-Drain Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	V <sub>DSF</sub>	I <sub>DR</sub> = 6.0 A, V <sub>GS</sub> = 0 V	-	0.90	1.2	V

Note 1: Pulse measurement.

#### 8. Marking

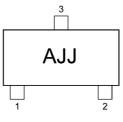
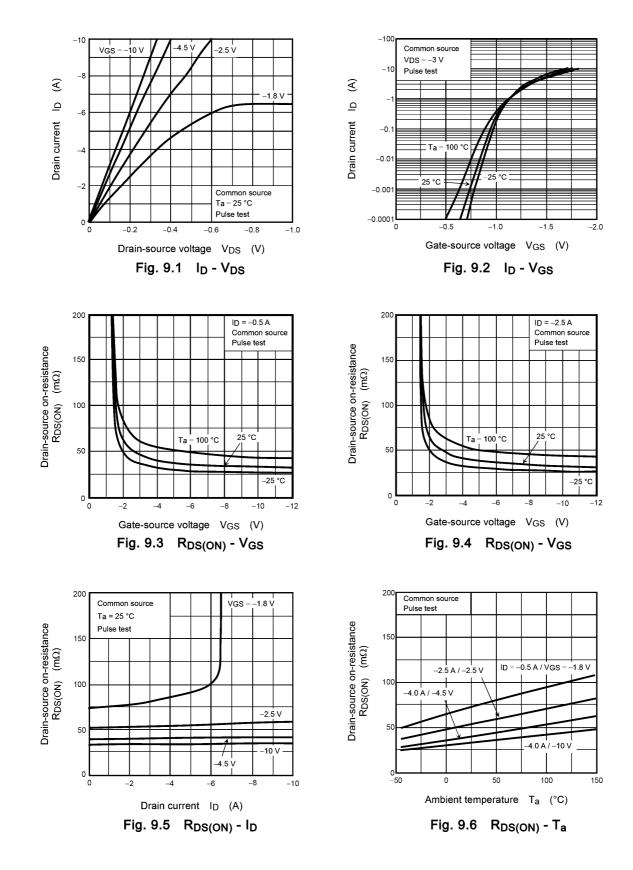


Fig. 8.1 Marking

#### 9. Characteristics Curves (Note)



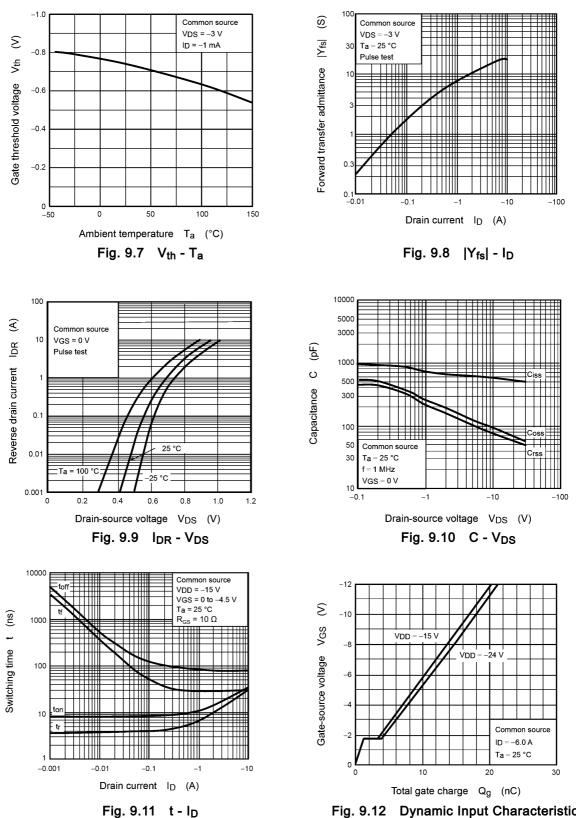


Fig. 9.12 Dynamic Input Characteristics

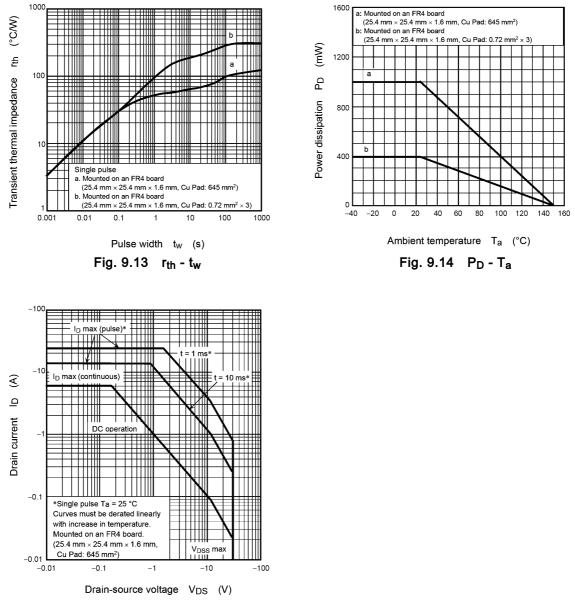


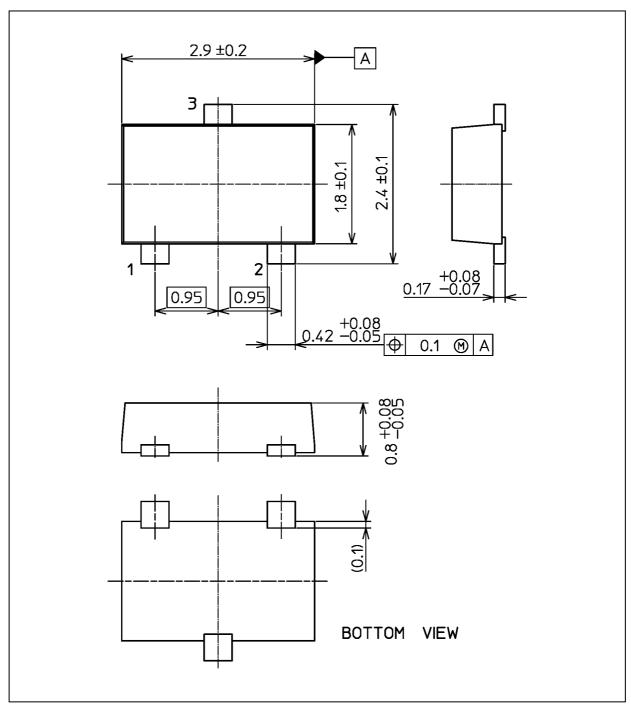
Fig. 9.15 Safe Operating Area

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



#### **Package Dimensions**

Unit: mm



Weight: 0.011 g (typ.)

Package Name(s)	
TOSHIBA: 2-3Z1S	
Nickname: SOT-23F	

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